

SiT8921B

High Frequency, -55°C to +125°C Oscillator



Features

- Frequencies between 119.342001 MHz to 137 MHz accurate to 6 decimal places
- Operating temperature from -55°C to 125°C
- Supply voltage of 1.8 V or 2.5 V to 3.3 V
- Excellent total frequency stability as low as ± 20 ppm
- Low power consumption of 4.9 mA typical at 1.8 V
- LVC MOS/LVTTL compatible output
- Industry-standard packages: 2.0 x 1.6, 2.5 x 2.0, 3.2 x 2.5, 5.0 x 3.2, 7.0 x 5.0 mm x mm
- Instant samples with [Time Machine II](#) and [field programmable oscillators](#)
- RoHS and REACH compliant, Pb-free, Halogen-free and Antimony-free

Applications

- Ruggedized equipment in harsh operating environment

Related products for [automotive applications](#).

For aerospace and defense applications SiTime recommends using only [Endura™ SiT8945](#).



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Table 1. Electrical Characteristics

All Min and Max limits are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at 25°C and nominal supply voltage.

Parameters	Symbol	Min.	Typ.	Max.	Unit	Condition
Frequency Range						
Output Frequency Range	f	119.342001	–	137	MHz	Refer to Table 13 for the exact list of supported frequencies
Frequency Stability and Aging						
Frequency Stability	F_stab	-20	–	+20	ppm	Inclusive of Initial tolerance at 25°C, 1st year aging at 25°C, and variations over operating temperature, rated power supply voltage and load (15 pF ± 10%).
		-25	–	+25	ppm	
		-30	–	+30	ppm	
		-50	–	+50	ppm	
Operating Temperature Range						
Operating Temperature Range	T_use	-55	–	+125	°C	
Supply Voltage and Current Consumption						
Supply Voltage	Vdd	1.62	1.8	1.98	V	
		2.25	2.5	2.75	V	
		2.52	2.8	3.08	V	
		2.7	3.0	3.3	V	
		2.97	3.3	3.63	V	
		2.25	–	3.63	V	
Current Consumption	Idd	–	6.2	8	mA	No load condition, f = 125 MHz, Vdd = 2.8 V, 3.0 V or 3.3 V
		–	5.4	7	mA	No load condition, f = 125 MHz, Vdd = 2.5 V
		–	4.9	6	mA	No load condition, f = 125 MHz, Vdd = 1.8 V
OE Disable Current	I_od	–	–	4.7	mA	Vdd = 2.5 V to 3.3 V, OE = Low, Output in high Z state.
		–	–	4.5	mA	Vdd = 1.8 V, OE = Low, Output in high Z state.
Standby Current	I_std	–	2.6	8.5	μA	Vdd = 2.8 V to 3.3V, \overline{ST} = Low, Output is weakly pulled down
		–	1.4	5.5	μA	Vdd = 2.5 V, \overline{ST} = Low, Output is weakly pulled down
		–	0.6	4.0	μA	Vdd = 1.8 V, \overline{ST} = Low, Output is weakly pulled down
LVCMOS Output Characteristics						
Duty Cycle	DC	45	–	55	%	All Vdds
Rise/Fall Time	Tr, Tf	–	1.0	2.0	ns	Vdd = 2.5 V, 2.8 V, 3.0 V or 3.3 V, 20% - 80%
		–	1.3	2.5	ns	Vdd =1.8 V, 20% - 80%
		–	1.0	3	ns	Vdd = 2.25 V - 3.63 V, 20% - 80%
Output High Voltage	VOH	90%	–	–	Vdd	IOH = -4 mA (Vdd = 3.0 V or 3.3 V) IOH = -3 mA (Vdd = 2.8 V or 2.5 V) IOH = -2 mA (Vdd = 1.8 V)
Output Low Voltage	VOL	–	–	10%	Vdd	IOL = 4 mA (Vdd = 3.0 V or 3.3 V) IOL = 3 mA (Vdd = 2.8 V or 2.5 V) IOL = 2 mA (Vdd = 1.8 V)

Table 1. Electrical Characteristics (continued)

Parameters	Symbol	Min.	Typ.	Max.	Unit	Condition
Input Characteristics						
Input High Voltage	V _{IH}	70%	–	–	V _{dd}	Pin 1, OE or \overline{ST}
Input Low Voltage	V _{IL}	–	–	30%	V _{dd}	Pin 1, OE or \overline{ST}
Input Pull-up Impedance	Z _{in}	50	87	150	kΩ	Pin 1, OE logic high or logic low, or \overline{ST} logic high
		2	–	–	MΩ	Pin 1, \overline{ST} logic low
Startup and Resume Timing						
Startup Time	T _{start}	–	–	5	ms	Measured from the time V _{dd} reaches its rated minimum value
Enable/Disable Time	T _{oe}	–	–	130	ns	f = 119.342001 MHz. For other frequencies, T _{oe} = 100 ns + 3 * clock periods
Resume Time	T _{resume}	–	–	5	ms	Measured from the time \overline{ST} pin crosses 50% threshold
Jitter						
RMS Period Jitter	T _{jitt}	–	1.6	2.5	ps	f = 125 MHz, V _{dd} = 2.5 V, 2.8 V, 3.0 V or 3.3 V
		–	1.8	3	ps	f = 125 MHz, V _{dd} = 1.8 V
Peak-to-peak Period Jitter	T _{pk}	–	12	20	ps	f = 125 MHz, V _{dd} = 2.5 V, 2.8 V, 3.0 V or 3.3 V
		–	14	25	ps	f = 125 MHz, V _{dd} = 1.8 V
RMS Phase Jitter (random)	T _{phj}	–	0.5	0.8	ps	f = 125 MHz, Integration bandwidth = 900 kHz to 7.5 MHz
		–	1.3	2	ps	f = 125 MHz, Integration bandwidth = 12 kHz to 20 MHz

Table 2. Pin Description

Pin	Symbol	Functionality	
1	OE/ \overline{ST} /NC	Output Enable	H ^[1] : specified frequency output L: output is high impedance. Only output driver is disabled.
		Standby	H ^[1] : specified frequency output L: output is low (weak pull down). Device goes to sleep mode. Supply current reduces to I _{std} .
		No Connect	Any voltage between 0 and V _{DD} or Open ^[1] : Specified frequency output. Pin 1 has no function.
2	GND	Power	Electrical ground
3	OUT	Output	Oscillator output
4	VDD	Power	Power supply voltage ^[2]

Notes:

- In OE or \overline{ST} mode, a pull-up resistor of 10 k Ω or less is recommended if pin 1 is not externally driven. If pin 1 needs to be left floating, use the NC option.
- A capacitor of value 0.1 μ F or higher between V_{DD} and GND is required.

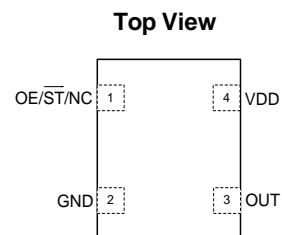


Figure 1. Pin Assignments

Table 3. Absolute Maximum Limits

Attempted operation outside the absolute maximum ratings of the part may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
VDD	-0.5	4	V
Electrostatic Discharge	–	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	–	260	°C
Junction Temperature ^[3]	–	150	°C

Note:

- Exceeding this temperature for extended period of time may damage the device.

Table 4. Thermal Consideration^[4]

Package	θ_{JA} , 4 Layer Board (°C/W)	θ_{JA} , 2 Layer Board (°C/W)	θ_{JC} , Bottom (°C/W)
7050	142	273	30
5032	97	199	24
3225	109	212	27
2520	117	222	26
2016	152	252	36

Note:

- Refer to JESD51-7 for θ_{JA} and θ_{JC} definitions, and reference layout used to determine the θ_{JA} and θ_{JC} values in the above table.

Table 5. Maximum Operating Junction Temperature^[5]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
125°C	135°C

Note:

- Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 6. Environmental Compliance

Parameter	Condition/Test Method
Mechanical Shock	MIL-STD-883F, Method2002
Mechanical Vibration	MIL-STD-883F, Method2007
Temperature Cycle	JESD22, Method A104
Solderability	MIL-STD-883F, Method2003
Moisture Sensitivity Level	MSL1 @ 260°C

Test Circuit and Waveform

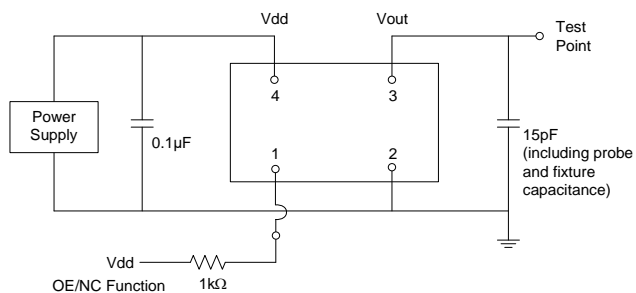


Figure 2. Test Circuit^[6]

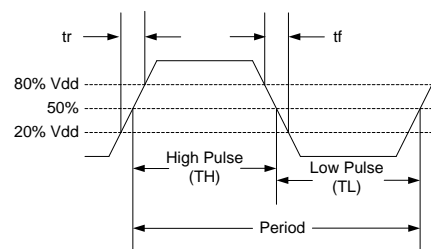


Figure 3. Waveform^[6]

Note:

6. Duty Cycle is computed as $\text{Duty Cycle} = \text{TH} / \text{Period}$.

Timing Diagram

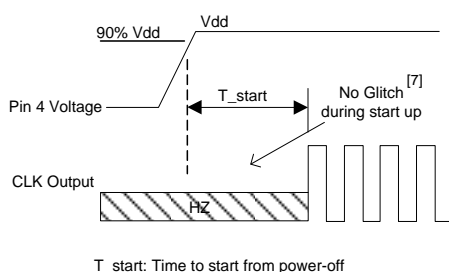


Figure 4. Startup Timing (OE/ST Mode)

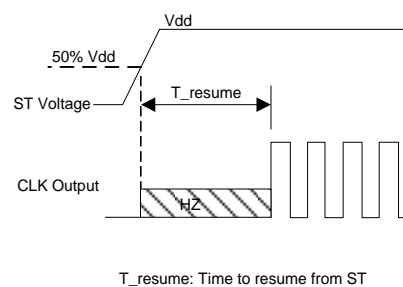


Figure 5. Standby Resume Timing (ST Mode Only)

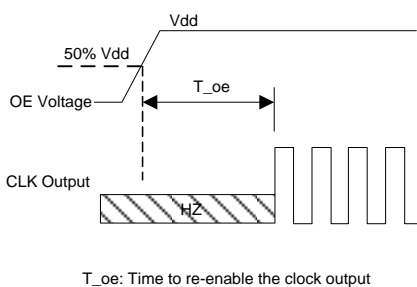


Figure 6. OE Enable Timing (OE Mode Only)

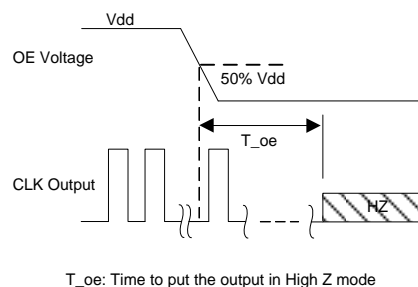


Figure 7. OE Disable Timing (OE Mode Only)

Note:

7. SiT8921 has “no runt” pulses and “no glitch” output during startup or resume.

Performance Plots^[8]

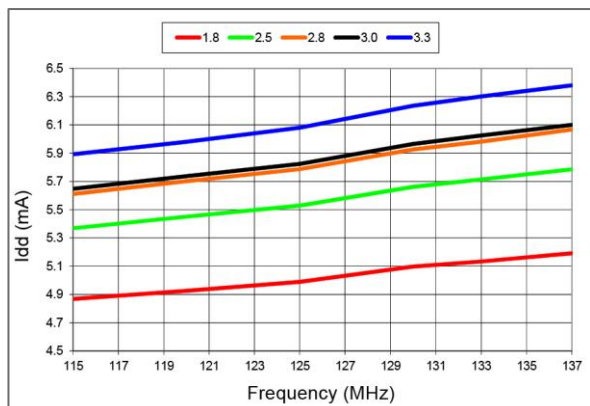


Figure 8. Idd vs Frequency

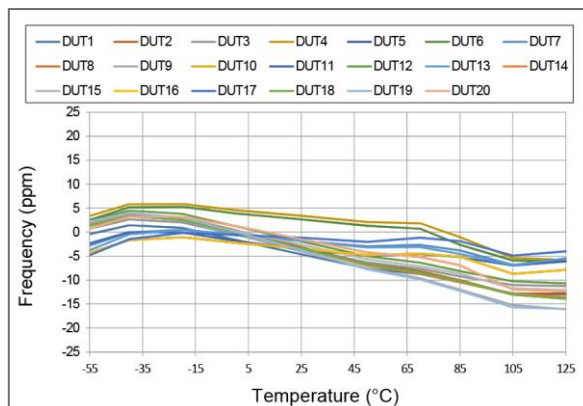


Figure 9. Frequency vs Temperature

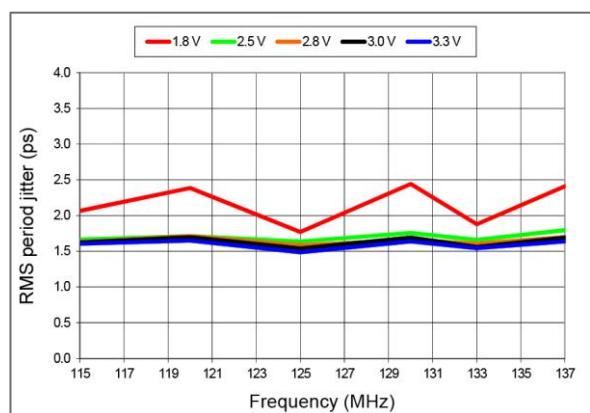


Figure 10. RMS Period Jitter vs Frequency

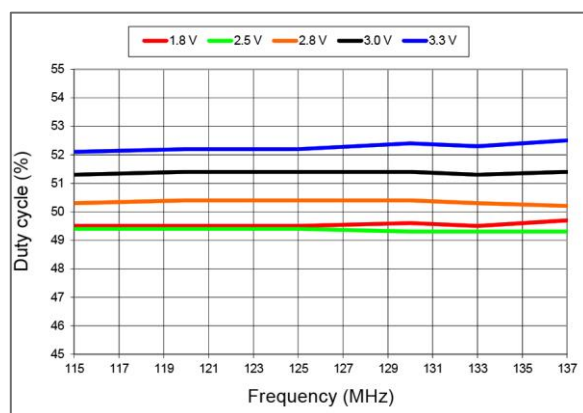
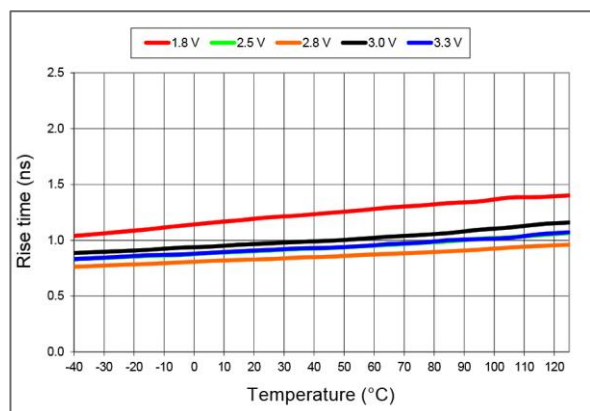
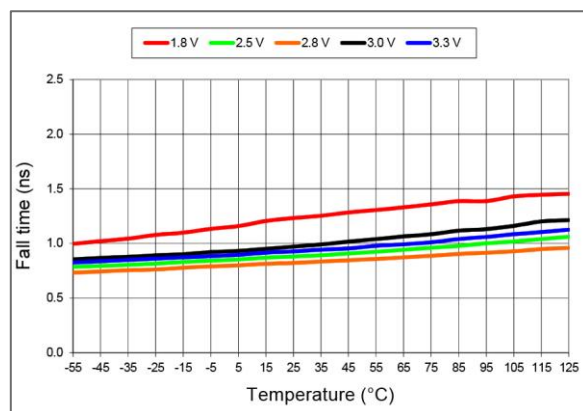


Figure 11. Duty Cycle vs Frequency



**Figure 12. 20%-80% Rise Time vs Temperature
(125 MHz Output)**



**Figure 13. 20%-80% Fall Time vs Temperature
(125 MHz Output)**

Performance Plots^[8] (continued)

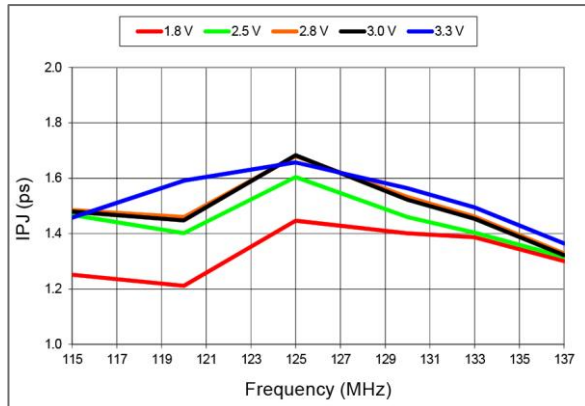


Figure 14. RMS Integrated Phase Jitter Random (12 kHz to 20 MHz) vs Frequency^[9]

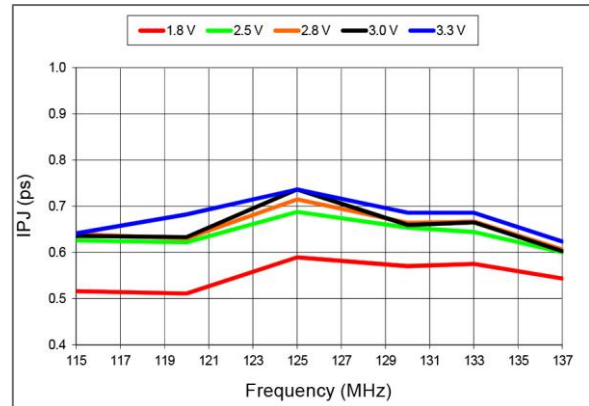


Figure 15. RMS Integrated Phase Jitter Random (900 kHz to 20 MHz) vs Frequency^[9]

Notes:

8. All plots are measured with 15 pF load at room temperature, unless otherwise stated.
9. Phase noise plots are measured with Agilent E5052B signal source analyzer.

Programmable Drive Strength

The SiT8921 includes a programmable drive strength feature to provide a simple, flexible tool to optimize the clock rise/fall time for specific applications. Benefits from the programmable drive strength feature are:

- Improves system radiated electromagnetic interference (EMI) by slowing down the clock rise/fall time
- Improves the downstream clock receiver's (RX) jitter by decreasing (speeding up) the clock rise/fall time.
- Ability to drive large capacitive loads while maintaining full swing with sharp edge rates.

For more detailed information about rise/fall time control and drive strength selection, see the [SiTime Application Notes](#) section.

EMI Reduction by Slowing Rise/Fall Time

Figure 16 shows the harmonic power reduction as the rise/fall times are increased (slowed down). The rise/fall times are expressed as a ratio of the clock period. For the ratio of 0.05, the signal is very close to a square wave. For the ratio of 0.45, the rise/fall times are very close to near-triangular waveform. These results, for example, show that the 11th clock harmonic can be reduced by 35 dB if the rise/fall edge is increased from 5% of the period to 45% of the period.

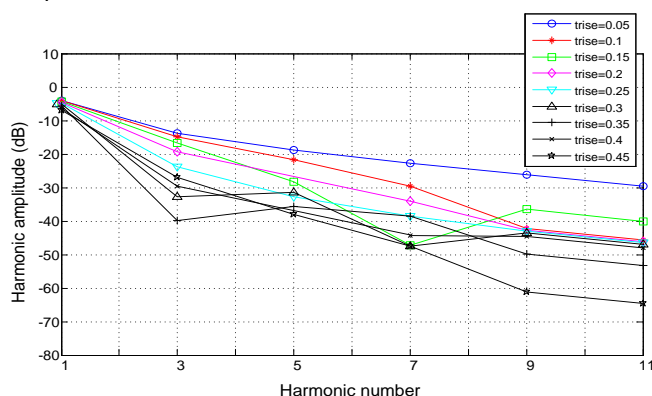


Figure 16. Harmonic EMI reduction as a Function of Slower Rise/Fall Time

Jitter Reduction with Faster Rise/Fall Time

Power supply noise can be a source of jitter for the downstream chipset. One way to reduce this jitter is to speed up the rise/fall time of the input clock. Some chipsets may also require faster rise/fall time in order to reduce their sensitivity to this type of jitter. Refer to the [Rise/Fall Time Tables \(Table 7 to 11\)](#) to determine the proper drive strength.

High Output Load Capability

The rise/fall time of the input clock varies as a function of the actual capacitive load the clock drives. At any given drive strength, the rise/fall time becomes slower as the output load increases. As an example, for a 3.3 V SiT8921 device with default drive strength setting, the typical rise/fall time is 0.46 ns for 5 pF output load. The typical rise/fall time slows down to 1 ns when the output load increases to 15 pF. One

can choose to speed up the rise/fall time to 0.72 ns by then increasing the driven strength setting on the SiT8921 to "F".

The SiT8921 can support up to 30 pF in maximum capacitive loads with up to 3 additional drive strength settings. Refer to the [Rise/Fall Time Tables \(Tables 7 to 11\)](#) to determine the proper drive strength for the desired combination of output load vs. rise/fall time.

SiT8921 Drive Strength Selection

Tables 7 through 11 define the rise/fall time for a given capacitive load and supply voltage.

1. Select the table that matches the SiT8921 nominal supply voltage (1.8 V, 2.5 V, 2.8 V, 3.0 V, 3.3 V).
2. Select the capacitive load column that matches the application requirement (5 pF to 30 pF)
3. Under the capacitive load column, select the desired rise/fall times.
4. The left-most column represents the part number code for the corresponding drive strength.
5. Add the drive strength code to the part number for ordering purposes.

Calculating Maximum Frequency

Based on the rise and fall time data given in [Tables 7 through 11](#), the maximum frequency the oscillator can operate with guaranteed full swing of the output voltage over temperature as follows:

$$\text{Max Frequency} = \frac{1}{5 \times \text{Trf}_{20/80}}$$

where Trf_{20/80} is the typical value for 20%-80% rise/fall time.

Example 1

Calculate fMAX for the following condition:

- Vdd = 3.3 V ([Table 11](#))
- Capacitive Load: 30 pF
- Desired Tr/f time = 1.46 ns (rise/fall time part number code = U)

Part number for the above example:

SiT8921BMU12-33E-136.986300



Drive strength code is inserted here. Default setting is "-".

Rise/Fall Time (20% to 80%) vs C_{LOAD} Tables

Table 7. V_{dd} = 1.8 V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C _{LOAD}	5 pF	15 pF	30 pF
T	0.93	n/a	n/a
E	0.78	n/a	n/a
U	0.70	1.48	n/a
F or "-": default	0.65	1.30	n/a

Table 9. V_{dd} = 2.5 V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C _{LOAD}	5 pF	15 pF	30 pF
R	1.45	n/a	n/a
B	1.09	n/a	n/a
T	0.62	1.28	n/a
E	0.54	1.00	n/a
U or "-": default	0.43	0.96	n/a
F	0.34	0.88	n/a

Table 8. V_{dd} = 2.8 V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C _{LOAD}	5 pF	15 pF	30 pF
R	1.29	n/a	n/a
B	0.97	n/a	n/a
T	0.55	1.12	n/a
E	0.44	1.00	n/a
U or "-": default	0.34	0.88	n/a
F	0.29	0.81	1.48

Table 10. V_{dd} = 3.0 V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C _{LOAD}	5 pF	15 pF	30 pF
R	1.22	n/a	n/a
B	0.89	n/a	n/a
T or "-": default	0.51	1.00	n/a
E	0.38	0.92	n/a
U	0.30	0.83	n/a
F	0.27	0.76	1.39

Table 11. V_{dd} = 3.3 V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)			
Drive Strength \ C _{LOAD}	5 pF	15 pF	30 pF
R	1.16	n/a	n/a
B	0.81	n/a	n/a
T or "-": default	0.46	1.00	n/a
E	0.33	0.87	n/a
U	0.28	0.79	1.46
F	0.25	0.72	1.31

Note:

10. "n/a" in Table 7 to Table 11 indicates that the resulting rise/fall time from the respective combination of the drive strength and output load does not provide rail-to-rail swing and is not available.

Pin 1 Configuration Options (OE, \overline{ST} , or NC)

Pin 1 of the SiT8921 can be factory-programmed to support three modes: Output enable (OE), standby (\overline{ST}) or No Connect (NC). These modes can also be programmed with the Time Machine using field programmable devices.

Output Enable (OE) Mode

In the OE mode, applying logic Low to the OE pin only disables the output driver and puts it in Hi-Z mode. The core of the device continues to operate normally. Power consumption is reduced due to the inactivity of the output. When the OE pin is pulled High, the output is typically enabled in <1 μ s.

Standby (\overline{ST}) Mode

In the \overline{ST} mode, a device enters into the standby mode when Pin 1 pulled Low. All internal circuits of the device are turned off. The current is reduced to a standby current, typically in the range of a few μ A. When \overline{ST} is pulled High, the device goes through the “resume” process, which can take up to 5 ms.

No Connect (NC) Mode

In the NC mode, the device always operates in its normal mode and output the specified frequency regardless of the logic level on pin 1.

Table 12 below summarizes the key relevant parameters in the operation of the device in OE, \overline{ST} , or NC mode.

Table 12. OE vs. \overline{ST} vs. NC

	OE	\overline{ST}	NC
Active current 125 MHz (max, 1.8 V)	6 mA	6 mA	6 mA
OE disable current (max, 1.8 V)	4.5 mA	N/A	N/A
Standby current (typical 1.8 V)	N/A	0.6 μ A	N/A
OE enable time at 125 MHz (max)	130 ns	N/A	N/A
Resume time from standby (max, all frequency)	N/A	5 ms	N/A
Output driver in OE disable/standby mode	High Z	Weak pull-down	N/A

Output on Startup and Resume

The SiT8921 comes with gated output. Its clock output is accurate to the rated frequency stability within the first pulse from initial device startup or resume from the standby mode.

In addition, the SiT8921 has NO RUNT, NO GLITCH output during startup or resume as shown in the waveform captures in Figure 17 and Figure 18.

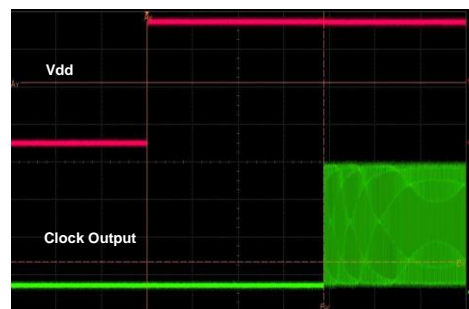
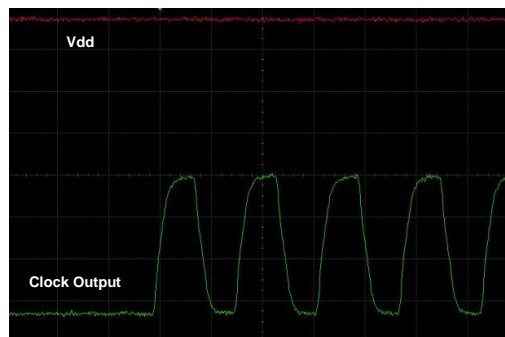


Figure 17. Startup Waveform vs. Vdd



**Figure 18. Startup Waveform vs. Vdd
(Zoomed-in View of Figure 17)**

Instant Samples with Time Machine and Field Programmable Oscillators

SiTime supports a field programmable version of the [SiT8921 high frequency, high temperature oscillator](#) for fast prototyping and real time customization of features. The [Field Programmable devices](#) (FP devices) are available for all five standard SiT8921 package sizes and can be configured to one's exact specification using the [Time Machine II](#), an USB powered MEMS oscillator programmer.

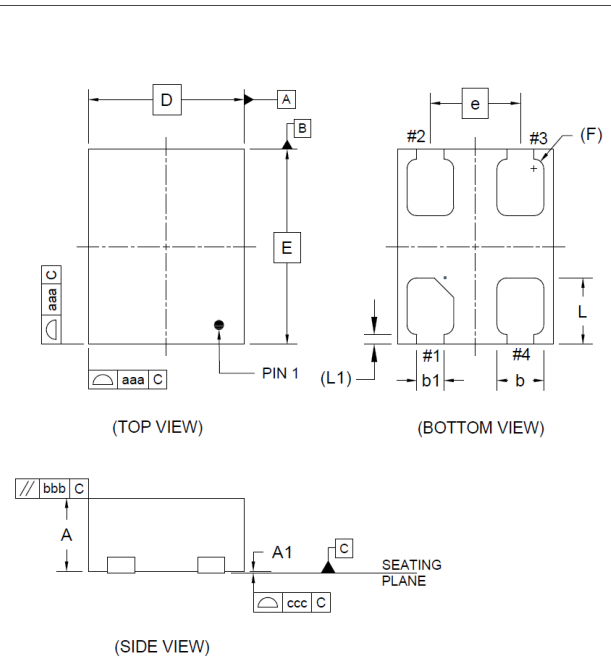

Customizable Features of the SiT8921 FP Devices Include

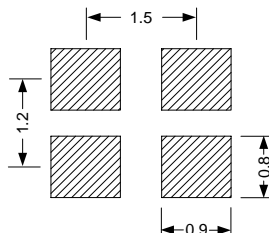
- Frequencies between 119.3420001 – 137 MHz
- Four frequency stability options, ± 20 ppm, ± 25 ppm, ± 30 ppm, ± 50 ppm
- Six supply voltage options, 1.8 V, 2.5 V, 2.8 V, 3.0 V, 3.3 V and 2.25 to 3.63 V continuous
- Output drive strength

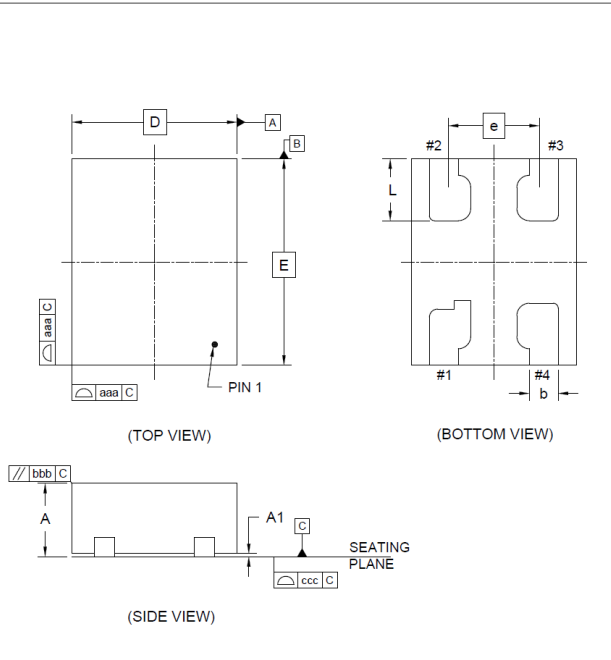

For more information regarding SiTime's field programmable solutions, visit [Time Machine II](#) and [Field Programmable devices](#).

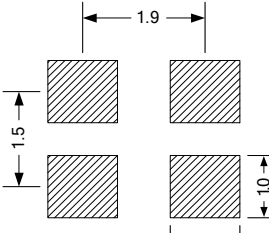
[SiT8921](#) is factory-programmed per customer ordering codes for volume delivery.

Dimensions and Patterns

Package Size – Dimensions (Unit: mm) ^[1]																	
2.0 x 1.6 x 0.75 mm																	
 <p>(TOP VIEW) (BOTTOM VIEW) (SIDE VIEW)</p>			SYMBOL	MIN	NOM	MAX											
			PACKAGE THICKNESS	A	0.700	0.750	0.800										
			STAND OFF	A1	0.000	0.020	0.050										
			BODY SIZE	X	D	1.600	BSC										
				Y	E	2.000	BSC										
			LEAD WIDTH	b	0.430	0.480	0.530										
				b1	0.230	0.280	0.330										
			LEAD LENGTH	L	0.580	0.680	0.780										
				L1		0.100	REF										
			LEAD PITCH	e		0.930	BSC										
			RADIUS	F		0.100	REF										
			PACKAGE TOLERANCE	aaa		0.050											
			MOLD FLATNESS	bbb		0.100											
			COPLANARITY	ccc		0.080											
			NOTES														
			1. Dimensioning and tolerance conform to ASME Y14.5-2009														
			2. All dimensions are in millimeters.														
		 <table> <tr> <td>TITLE</td><td>4L PQFN</td><td colspan="2">DWG NO.</td></tr> <tr> <td></td><td>1.60x2.00x0.75 mm</td><td>REV.</td><td>SHEET</td></tr> <tr> <td>DATE</td><td>01-APR-2019</td><td>A02</td><td>1 OF 2</td></tr> </table>				TITLE	4L PQFN	DWG NO.			1.60x2.00x0.75 mm	REV.	SHEET	DATE	01-APR-2019	A02	1 OF 2
TITLE	4L PQFN	DWG NO.															
	1.60x2.00x0.75 mm	REV.	SHEET														
DATE	01-APR-2019	A02	1 OF 2														

Recommended Land Pattern (Unit: mm) ^[12]					
					

Package Size – Dimensions (Unit: mm) ^[1]															
2.5 x 2.0 x 0.75 mm															
 <p>(TOP VIEW) (BOTTOM VIEW) (SIDE VIEW)</p>			SYMBOL	MIN	NOM	MAX									
			PACKAGE THICKNESS	A	0.700	0.750	0.800								
			THICKNESS	A1	0.000	0.020	0.050								
			BODY SIZE	X	D	2.000	BSC								
				Y	E	2.500	BSC								
			LEAD WIDTH	b	0.300	0.350	0.400								
				L	0.650	0.750	0.850								
			LEAD PITCH	e		1.250	BSC								
			PACKAGE TOLERANCE	aaa		0.050									
			MOLD FLATNESS	bbb		0.100									
			COPLANARITY	ccc		0.080									
			NOTES												
			1. Dimensioning and tolerance conform to ASME Y14.5-2009												
			2. All dimensions are in millimeters.												
		 <table> <tr> <td>TITLE</td><td>4L PQFN</td><td colspan="2">DWG NO.</td></tr> <tr> <td></td><td>2.00x2.50x0.75 mm</td><td>REV.</td><td>SHEET</td></tr> <tr> <td>DATE</td><td>01-APR-2019</td><td>A02</td><td>1 OF 2</td></tr> </table>				TITLE	4L PQFN	DWG NO.			2.00x2.50x0.75 mm	REV.	SHEET	DATE	01-APR-2019
TITLE	4L PQFN	DWG NO.													
	2.00x2.50x0.75 mm	REV.	SHEET												
DATE	01-APR-2019	A02	1 OF 2												

Recommended Land Pattern (Unit: mm) ^[12]					
					

Dimensions and Patterns (continued)

Package Size – Dimensions (Unit: mm)^[1]

Recommended Land Pattern (Unit: mm)^[12]

3.2 x 2.5 x 0.75 mm

Technical drawing of a 3.2 x 2.5 x 0.75 mm package. The drawing includes three views: TOP VIEW, BOTTOM VIEW, and SIDE VIEW. Dimensions are labeled: D (body width), A (body length), E (lead pitch), B (lead width), C (lead length), A1 (stand-off), L (lead length), L1 (lead length), F (radius), e (lead pitch), b (lead width), and PIN 1. The table below provides the dimensions in millimeters.

	SYMBOL	MIN	NOM	MAX
PACKAGE THICKNESS	A	0.700	0.750	0.800
STAND OFF	A1	0.000	0.020	0.050
BODY SIZE	X	D	2.500	BSC
	Y	E	3.200	BSC
LEAD WIDTH	b	0.800	0.900	1.000
LEAD LENGTH	L	0.700	0.800	0.900
	L1	0.100	REF	
LEAD PITCH	e	2.100	BSC	
RADIUS	F	0.450	REF	
	F1	0.120	REF	
PACKAGE TOLERANCE	aaa	0.050		
MOLD FLATNESS	bbb	0.100		
COPLANARITY	ccc	0.080		

NOTES

1. Dimensioning and tolerance conform to ASME Y14.5-2009.

2. All dimensions are in millimeters.

SiTime

TITLE: 4L PQFN DWG NO.: POD-PQFN-004-X03225-002

3.20x2.50x0.75 mm REV.: SHEET

DATE: 01-APR-2019 A04 1 OF 2

Recommended land pattern for the 3.2 x 2.5 x 0.75 mm package. The pattern shows a 2x2 grid of pads. Dimensions are: 2.2 mm (pad width), 1.9 mm (pad height), 1.2 mm (pad height), and 1.4 mm (pad width).

5.0 x 3.2 x 0.75 mm

Technical drawing of a 5.0 x 3.2 x 0.75 mm package. The drawing includes three views: TOP VIEW, BOTTOM VIEW, and SIDE VIEW. Dimensions are labeled: D (body width), A (body length), E (lead pitch), B (lead width), C (lead length), A1 (stand-off), L (lead length), L1 (lead length), F (radius), e (lead pitch), b (lead width), and PIN 1. The table below provides the dimensions in millimeters.

	SYMBOL	MIN	NOM	MAX
PACKAGE THICKNESS	A	0.700	0.750	0.800
STAND OFF	A1	0.000	0.020	0.050
BODY SIZE	X	D	3.200	BSC
	Y	E	5.000	BSC
LEAD WIDTH	b	1.000	1.100	1.200
LEAD LENGTH	L	1.050	1.100	1.150
	L1	1.200	REF	
LEAD PITCH	e	2.390	BSC	
RADIUS	F	0.575		
PACKAGE TOLERANCE	aaa	0.050		
MOLD FLATNESS	bbb	0.100		
COPLANARITY	ccc	0.080		

NOTES

1. Dimensioning and tolerance conform to ASME Y14.5-2009.

2. All dimensions are in millimeters.

SiTime

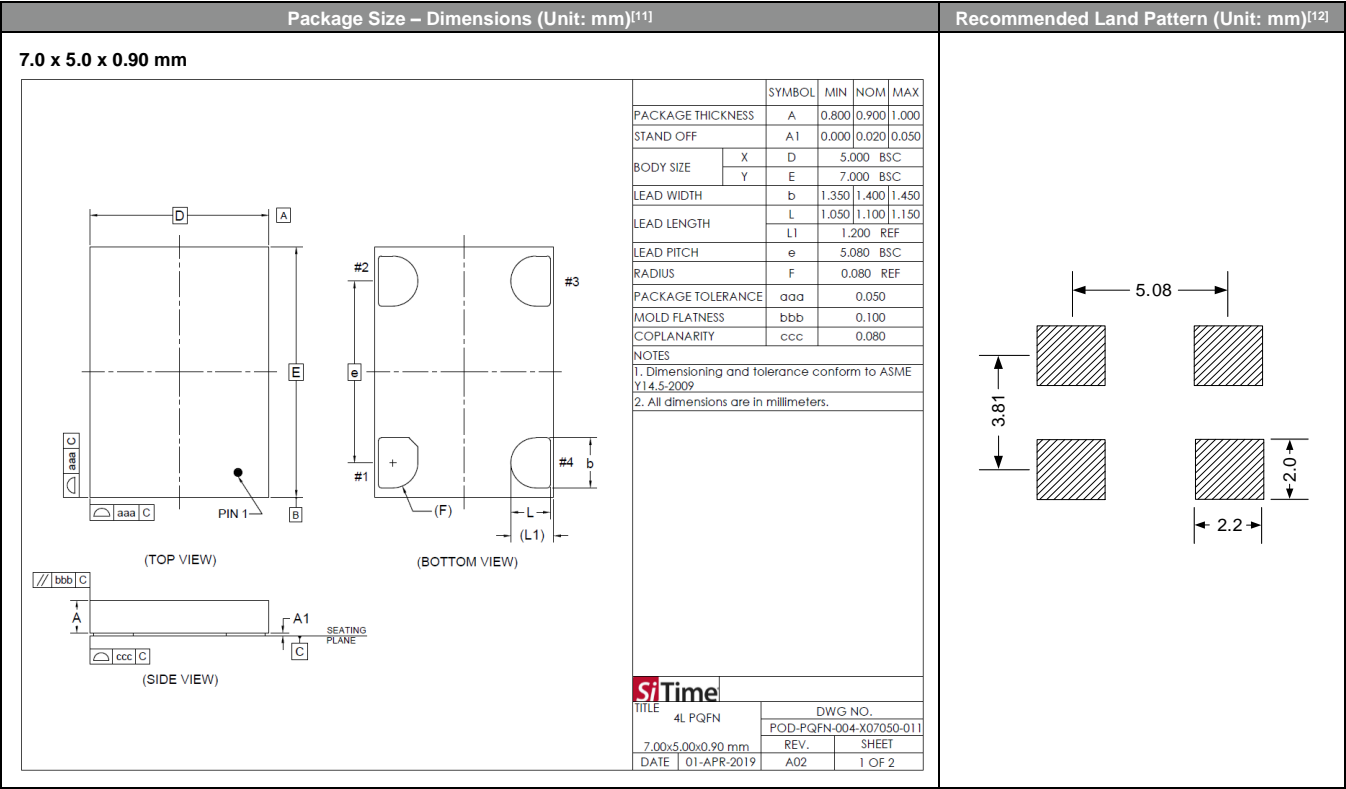
TITLE: 4L PQFN DWG NO.: POD-PQFN-004-X05032-003

5.00x3.20x0.75 mm REV.: SHEET

DATE: 01-APR-2019 A04 1 OF 2

Recommended land pattern for the 5.0 x 3.2 x 0.75 mm package. The pattern shows a 2x2 grid of pads. Dimensions are: 2.54 mm (pad width), 2.2 mm (pad height), 1.6 mm (pad height), and 1.5 mm (pad width).

Dimensions and Patterns (continued)



- Notes:
- 11. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of “Y” will depend on the assembly location of the device.
 - 12. A capacitor of value 0.1 μ F or higher between Vdd and GND is required.

Ordering Information

The Part No. Guide is for reference only. To customize and build an exact part number, use the [SiTime Part Number Generator](#).

SiT8921BM-12-18E - 25.000625D

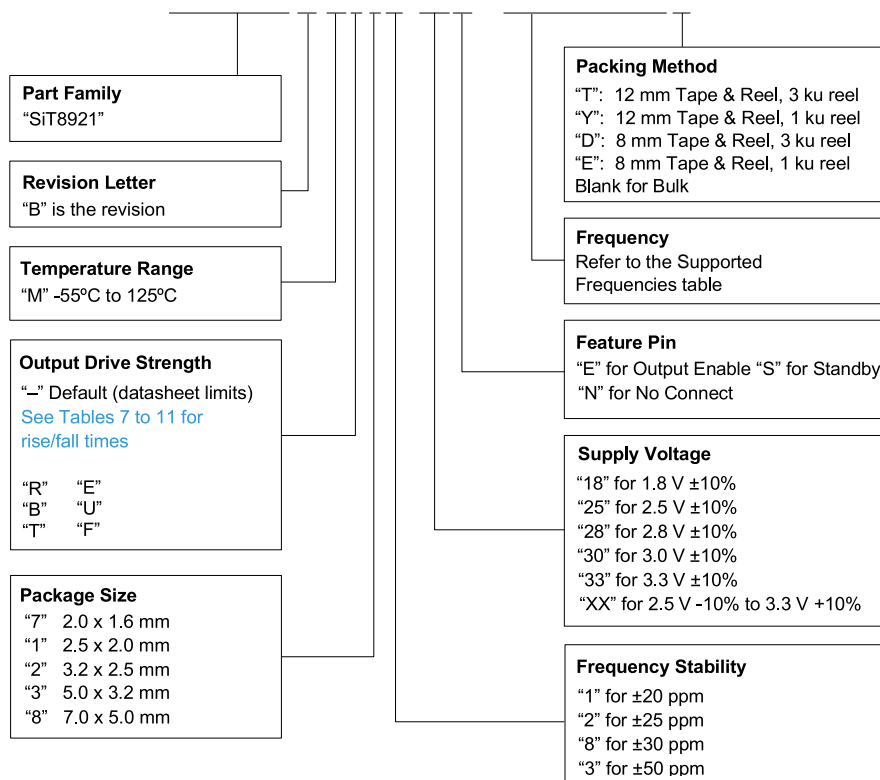


Table 13. List of Supported Frequencies^[13, 14]

Frequency Range (-55 to +125°C)	
Min.	Max.
119.342001 MHz	120.238999 MHz
120.262001 MHz	121.169999 MHz
121.243001 MHz	121.600999 MHz
123.948001 MHz	137.000000 MHz

Notes:

13. Any frequency within the min and max values in the above table are supported with 6 decimal places of accuracy.
14. Please contact SiTime for frequencies that are not listed in the tables above.

Table 14. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	16 mm T&R (3ku)	16 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	8 mm T&R (3ku)	8 mm T&R (1ku)
2.0 x 1.6	—	—	—	—	D	E
2.5 x 2.0	—	—	—	—	D	E
3.2 x 2.5	—	—	—	—	D	E
5.0 x 3.2	—	—	T	Y	—	—
7.0 x 5.0	T	Y	—	—	—	—

Table 15. Additional Information

Document	Description	Download Link
Time Machine II	MEMS oscillator programmer	http://www.sitime.com/support/time-machine-oscillator-programmer
Field Programmable Oscillators	Devices that can be programmable in the field by Time Machine II	http://www.sitime.com/products/field-programmable-oscillators
Manufacturing Notes	Tape & Reel dimension, reflow profile and other manufacturing related info	https://www.sitime.com/sites/default/files/gated/Manufacturing-Notes-for-SiTime-Products.pdf
Qualification Reports	RoHS report, reliability reports, composition reports	http://www.sitime.com/support/quality-and-reliability
Performance Reports	Additional performance data such as phase noise, current consumption and jitter for selected frequencies	http://www.sitime.com/support/performance-measurement-report
Termination Techniques	Termination design recommendations	http://www.sitime.com/support/application-notes
Layout Techniques	Layout recommendations	http://www.sitime.com/support/application-notes

Table 16. Revision History

Version	Release Date	Change Summary
1.0	7-May-2015	Final production release
1.01	2-Jan-2017	Added 16 mm T&R information to Table 14 Revised 12 mm T&R information to Table 14
1.02	15-Jun-2021	Updated logo and company address, other page layout changes Updated Dimensions and Patterns package drawings
1.03	1-Jan-2023	Updated company disclaimer, links, references and icons

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For aerospace and defense applications, SiTime recommends using only [Endura™ ruggedized products](#).

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Supplemental Information

The Supplemental Information section is not part of the datasheet and is for informational purposes only.

Best Reliability

Silicon is inherently more reliable than quartz. Unlike quartz suppliers, SiTime has in-house MEMS and analog CMOS expertise, which allows SiTime to develop the most reliable products. Figure 1 shows a comparison with quartz technology.

Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal® process, which eliminates foreign particles and improves long term aging and reliability
- World-class MEMS and CMOS design expertise

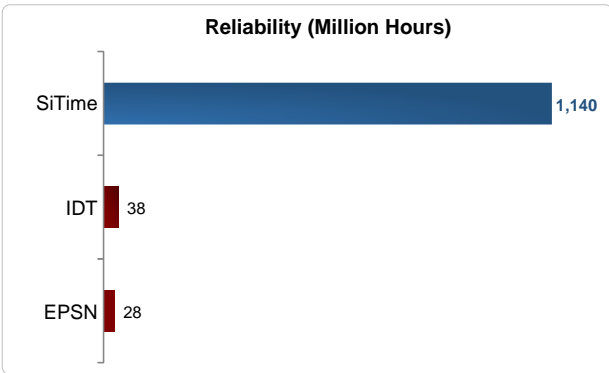


Figure 1. Reliability Comparison^[1]

Best Aging

Unlike quartz, MEMS oscillators have excellent long term aging performance which is why every new SiTime product specifies 10-year aging. A comparison is shown in Figure 2.

Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal® process, which eliminates foreign particles and improves long term aging and reliability
- Inherently better immunity of electrostatically driven MEMS resonator

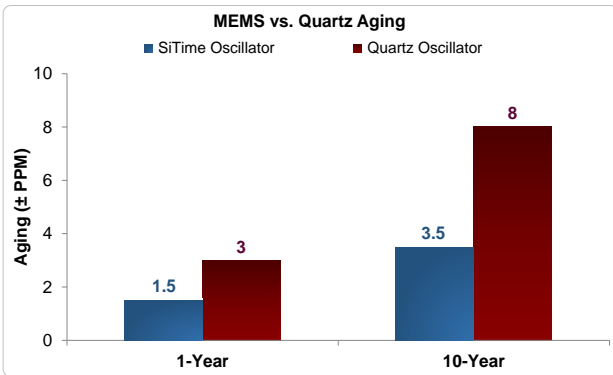


Figure 2. Aging Comparison^[2]

Best Electro Magnetic Susceptibility (EMS)

SiTime's oscillators in plastic packages are up to 54 times more immune to external electromagnetic fields than quartz oscillators as shown in Figure 3.

Why is SiTime Best in Class:

- Internal differential architecture for best common mode noise rejection
- Electrostatically driven MEMS resonator is more immune to EMS

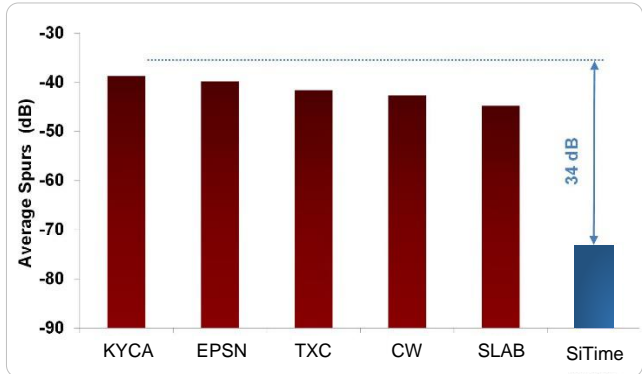


Figure 3. Electro Magnetic Susceptibility (EMS)^[3]

Best Power Supply Noise Rejection

SiTime's MEMS oscillators are more resilient against noise on the power supply. A comparison is shown in Figure 4.

Why is SiTime Best in Class:

- On-chip regulators and internal differential architecture for common mode noise rejection
- MEMS resonator is paired with advanced analog CMOS IC

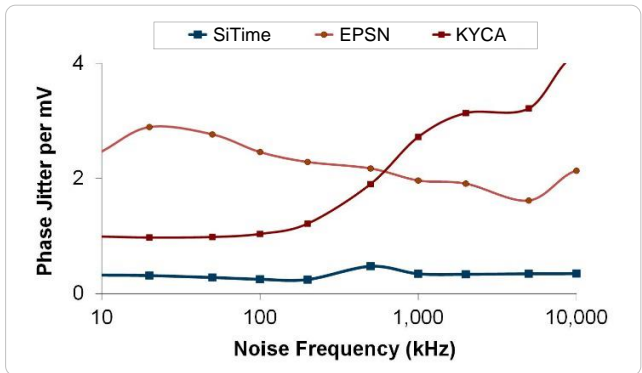


Figure 4. Power Supply Noise Rejection^[4]

Best Vibration Robustness

High-vibration environments are all around us. All electronics, from handheld devices to enterprise servers and storage systems are subject to vibration. Figure 5 shows a comparison of vibration robustness.

Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than quartz
- Center-anchored MEMS resonator is the most robust design

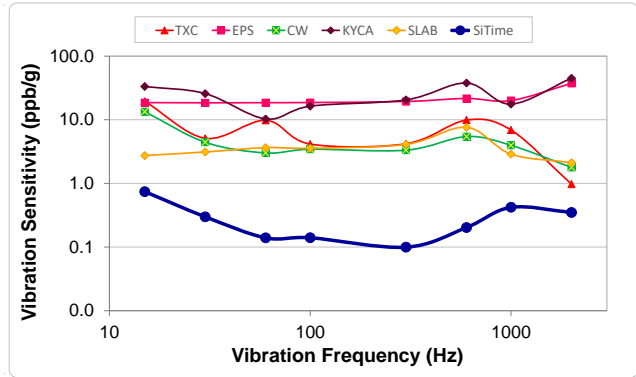


Figure 16. Vibration Robustness^[5]

Figure labels:

- TXC = TXC
- Epson = EPSN
- Connor Winfield = CW
- Kyocera = KYCA
- SiLabs = SLAB
- SiTime = EpiSeal MEMS

Best Shock Robustness

SiTime's oscillators can withstand at least 50,000 g shock. They all maintain their electrical performance in operation during shock events. A comparison with quartz devices is shown in Figure 6.

Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than quartz
- Center-anchored MEMS resonator is the most robust design

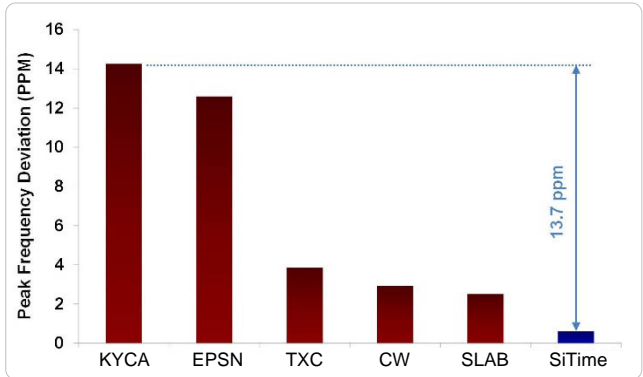


Figure 17. Shock Robustness^[6]

Notes:

1. Data source: Reliability documents of named companies.
2. Data source: SiTime and quartz oscillator devices datasheets.
3. Test conditions for Electro Magnetic Susceptibility (EMS):
 - According to IEC EN61000-4.3 (Electromagnetic compatibility standard)
 - Field strength: 3V/m
 - Radiated signal modulation: AM 1 kHz at 80% depth
 - Carrier frequency scan: 80 MHz – 1 GHz in 1% steps
 - Antenna polarization: Vertical
 - DUT position: Center aligned to antenna

Devices used in this test:

Label	Manufacturer	Part Number	Technology
EpiSeal MEMS	SiTime	SiT9120AC-1D2-33E156.250000	MEMS + PLL
EPSN	Epson	EG-2102CA156.2500M-PHPAL3	Quartz, SAW
TXC	TXC	BB-156.250MBE-T	Quartz, 3 rd Overtone
CW	Conner Winfield	P123-156.25M	Quartz, 3 rd Overtone
KYCA	AVX Kyocera	KC7050T156.250P30E00	Quartz, SAW
SLAB	SiLab	590AB-BDG	Quartz, 3 rd Overtone + PLL

4. 50 mV pk-pk Sinusoidal voltage.

Devices used in this test:

Label	Manufacturer	Part Number	Technology
EpiSeal MEMS	SiTime	SiT8208AI-33-33E-25.000000	MEMS + PLL
NDK	NDK	NZ2523SB-25.6M	Quartz
KYCA	AVX Kyocera	KC2016B25M0C1GE00	Quartz
EPSN	Epson	SG-310SCF-25M0-MB3	Quartz

5. Devices used in this test:
same as EMS test stated in Note 3.
6. Test conditions for shock test:
 - MIL-STD-883F Method 2002
 - Condition A: half sine wave shock pulse, 500-g, 1ms
 - Continuous frequency measurement in 100 μ s gate time for 10 seconds

Devices used in this test:

same as EMS test stated in Note 3.

7. Additional data, including setup and detailed results, is available upon request to qualified customer. Please contact productsupport@sitime.com.